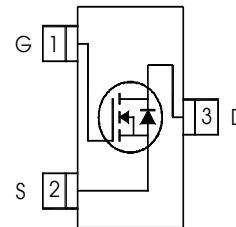
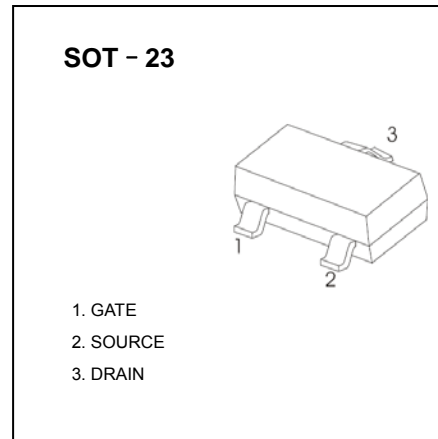


**Features**

- $V_{DS} (V) = 30V$
- $R_{DS(ON)} < 250m\Omega$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 400m\Omega$  ( $V_{GS} = 4.5V$ )

**Description**

- Generation VTechnology UltraLowOn- Resistance
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free
- RoHS CompliantHalogen-Free



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	1.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	0.93	
$I_{DM}$	Pulsed Drain Current ①	7.3	
$P_D @ T_A = 25^\circ C$	Power Dissipation	540	mW
	Linear Derating Factor	4.3	mW/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ⑤	3.9	mJ
$dv/dt$	Peak diode Recovery $dv/dt$ ②	5.0	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

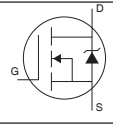
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	230	°C/W

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	250	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.91A ③
		—	—	400		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.46A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	0.87	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.46A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	25		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge	—	3.3	5.0	nC	I <sub>n</sub> = 0.91A
Q <sub>gs</sub>	Gate-to-Source Charge	—	0.48	0.72		V <sub>DS</sub> = 24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	1.1	1.7		V <sub>GS</sub> = 10V, See Fig. 6 and 9 ③
t <sub>d(on)</sub>	Turn-On Delay Time	—	3.9	—	ns	V <sub>DD</sub> = 15V
t <sub>r</sub>	Rise Time	—	4.0	—		I <sub>n</sub> = 0.91A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	9.0	—		R <sub>G</sub> = 6.2Ω
t <sub>f</sub>	Fall Time	—	1.7	—		R <sub>D</sub> = 16Ω, See Fig. 10 ③
C <sub>iss</sub>	Input Capacitance	—	85	—	pF	V <sub>DS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	34	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	15	—		f = 1.0MHz, See Fig. 5

**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	0.54	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	7.3		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 0.91A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	26	40	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 0.91A
Q <sub>rr</sub>	Reverse Recovery Charge	—	22	32	nC	di/dt = 100A/μs ③

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② I<sub>SD</sub> ≤ 0.91A, di/dt ≤ 120A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 150°C
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ Surface mounted on FR-4 board, t ≤ 5sec.
- ⑤ Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 9.4mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 0.9A.

Typical Electrical Characteristics

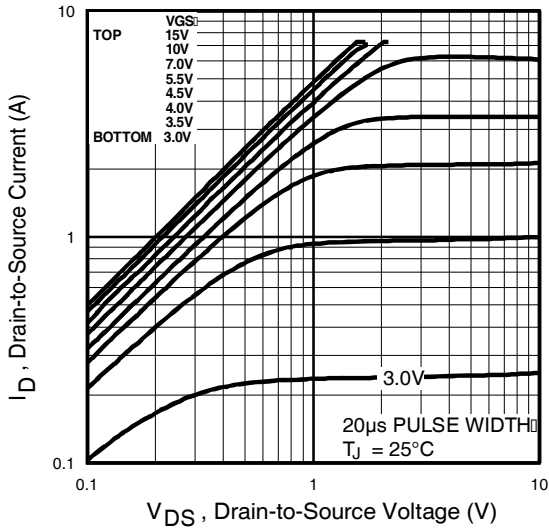


Fig 1. Typical Output Characteristics

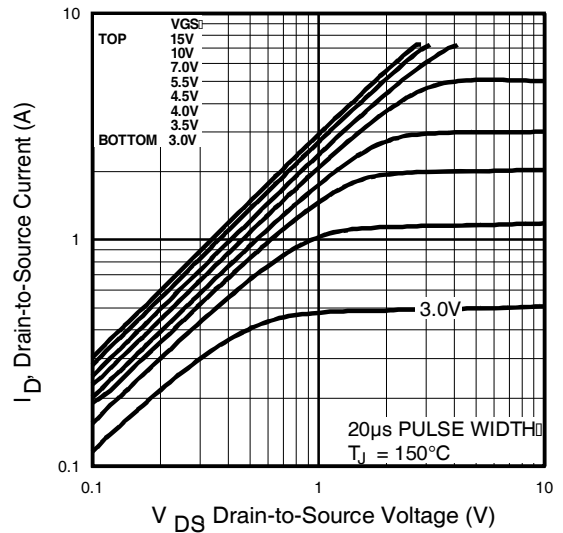


Fig 2. Typical Output Characteristics

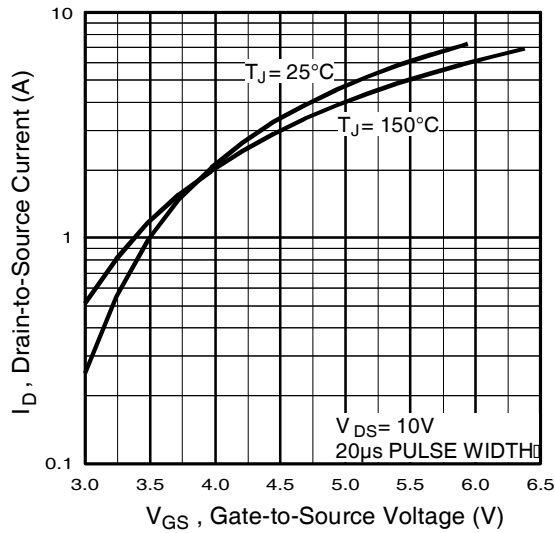


Fig 3. Typical Transfer Characteristics

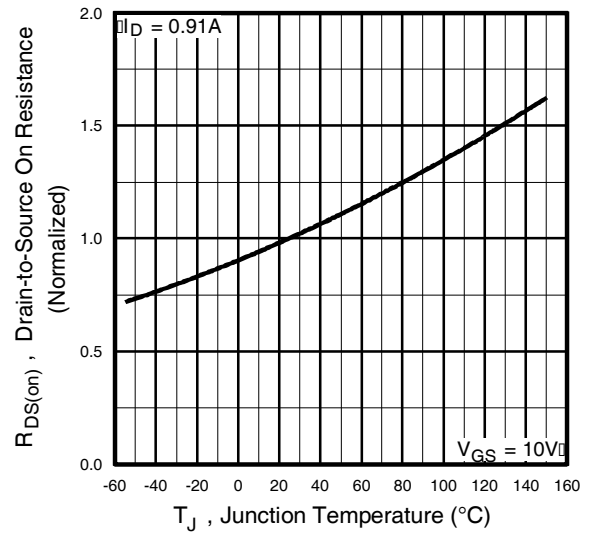


Fig 4. Normalized On-Resistance Vs. Temperature

Typical Electrical Characteristics

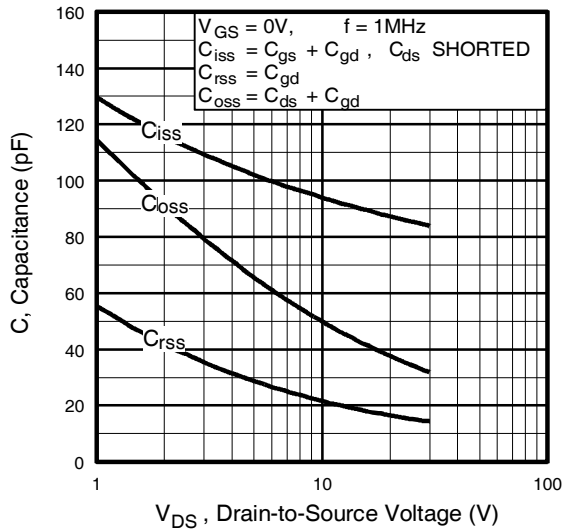


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

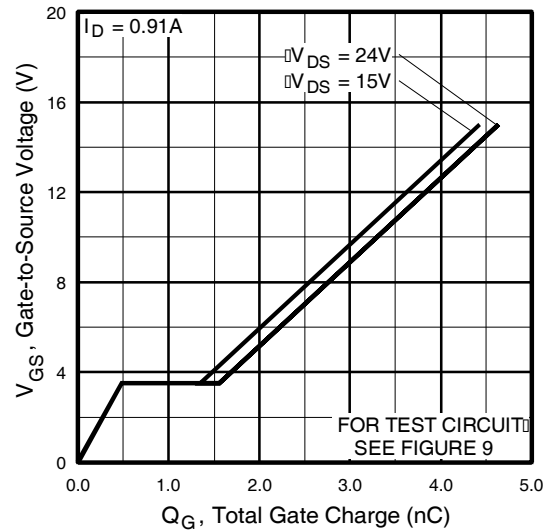


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

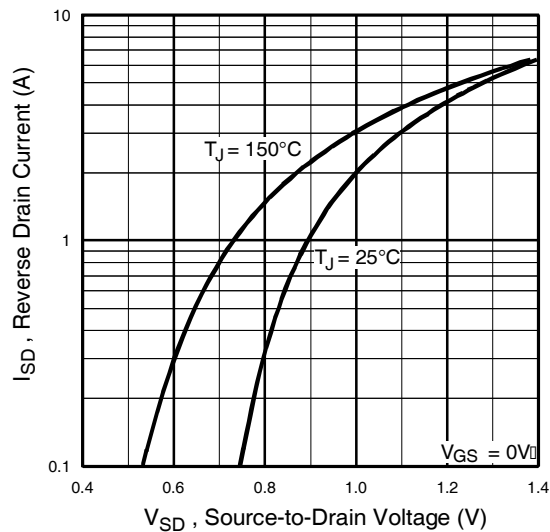


Fig 7. Typical Source-Drain Diode Forward Voltage

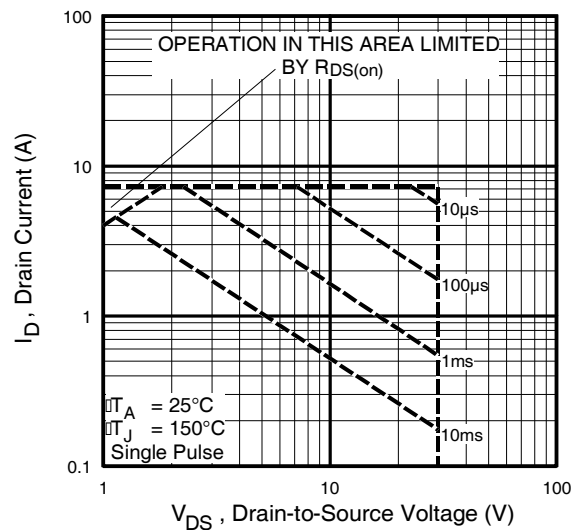


Fig 8. Maximum Safe Operating Area

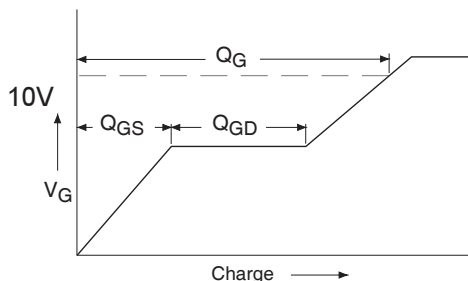


Fig 9a. Basic Gate Charge Waveform

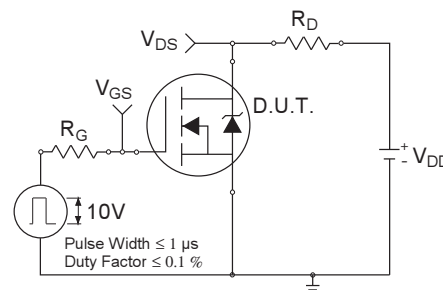


Fig 10a. Switching Time Test Circuit

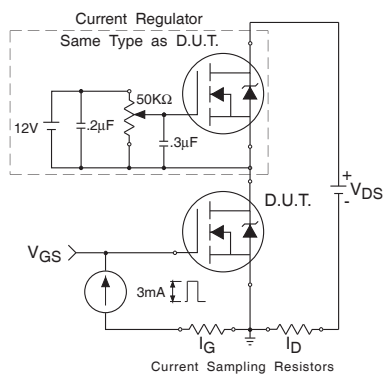


Fig 9b. Gate Charge Test Circuit

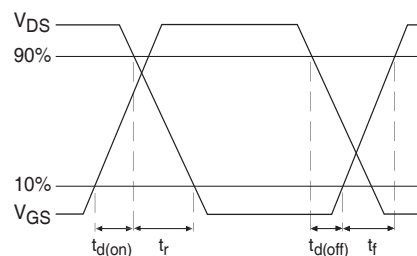


Fig 10b. Switching Time Waveforms

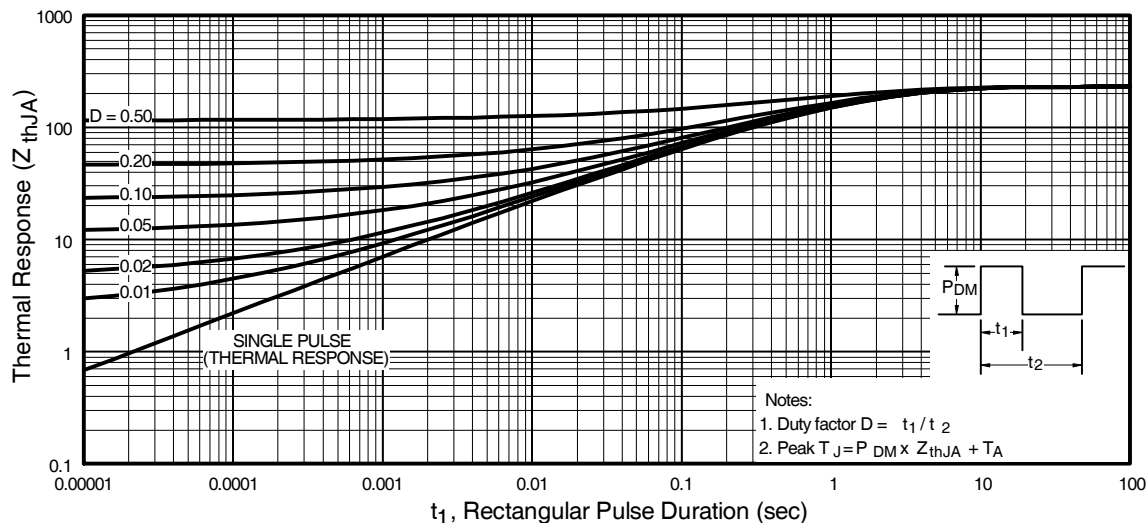


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

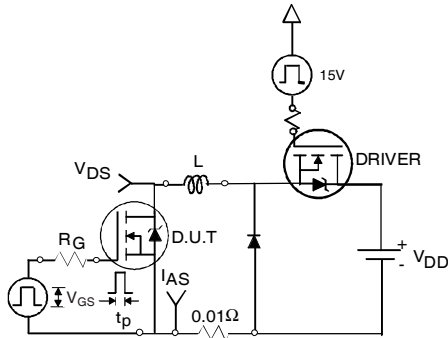


Fig 12a. Unclamped Inductive Test Circuit

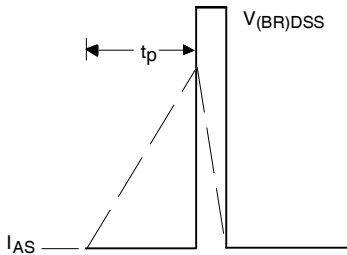


Fig 12b. Unclamped Inductive Waveforms

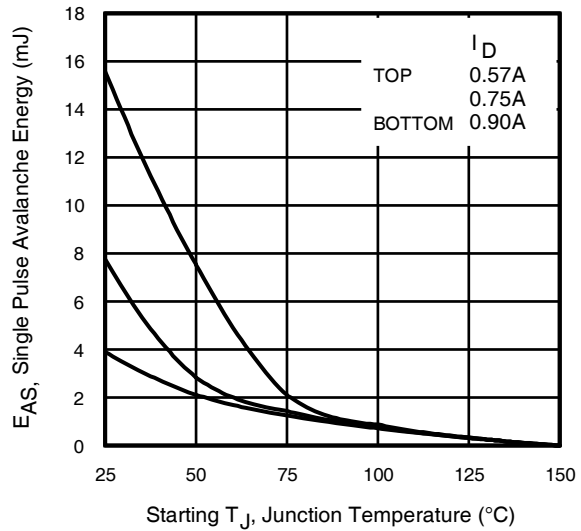
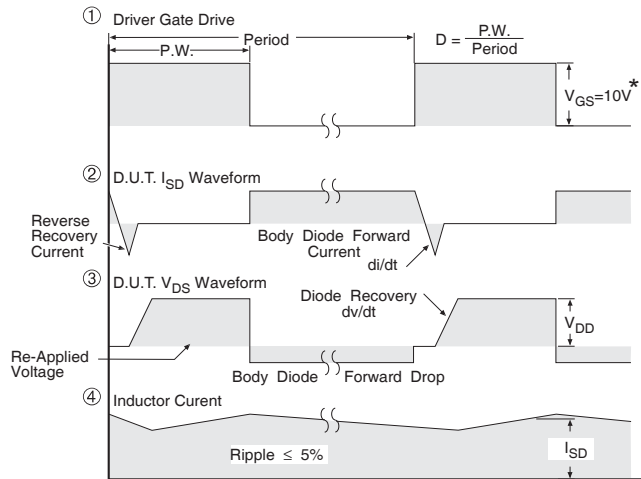
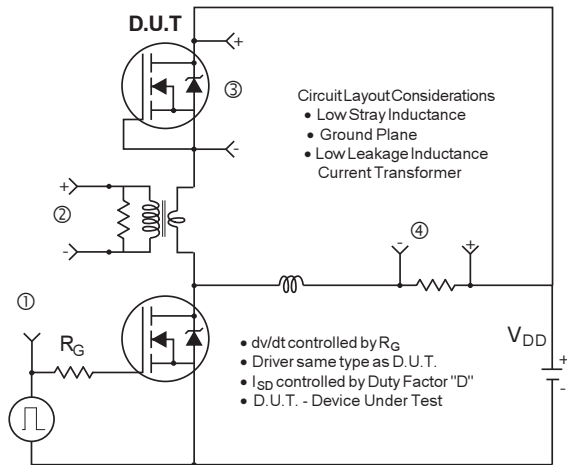


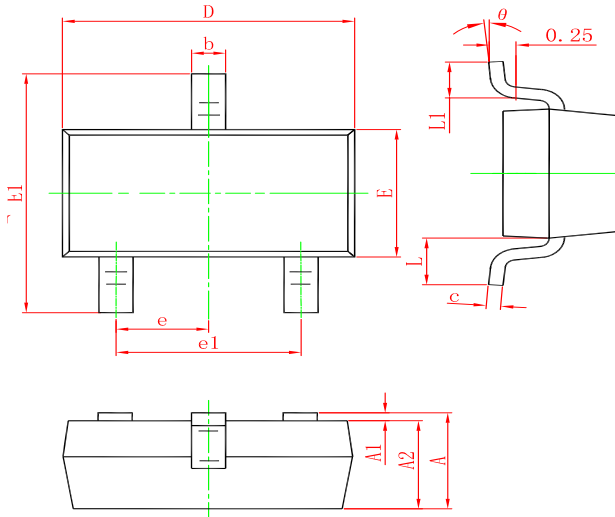
Fig 12c. Maximum Avalanche Energy vs. Drain Current



\*  $V_{GS} = 5V$  for Logic Level Devices

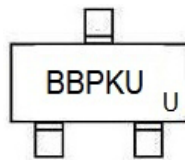
Fig 13. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET<sup>®</sup> Power MOSFETs

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRLML2803TR	SOT-23	3000	Tape and reel